

a liner comprising a compound including silicon and carbon, the liner positioned between at least a portion of the dielectric layer and a conductive element.

B' 2. (amended) The integrated circuit structure of Claim 1, wherein the liner is selected from the group consisting of silicon carbide, silicon oxy-carbide, and silicon boron-carbide.

B² 11. (amended) An integrated circuit structure comprising a liner positioned between at least a portion of a dielectric layer and a conductive element, the liner comprising a compound including silicon and carbon.

12. (amended) The integrated circuit structure of Claim 11, wherein the liner is selected from the group consisting of silicon carbide, silicon oxy-carbide, and silicon boron-carbide.
